

# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

## Title of Invention

NON-DESTRUCTIVE EVALUATION OF MICROSTRUCTURE  
AND INTERFACE ROUGHNESS OF ELECTRICALLY  
CONDUCTING LINES IN SEMICONDUCTOR INTEGRATED  
CIRCUITS IN DEEP SUB-MICRON REGIME

Application Number :

Confirmation Number:

First Named Applicant: Fen Chen

Attorney Docket Number: BUR920040182US1

Art Unit:

Examiner:

Search string: ( 6603321 or 20010046276 ).pn

## US Patent Documents

**Note: Applicant is not required to submit a paper copy of cited US Patent Documents**

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6603321	2003-08-05	Filippi, Jr. et al			

## US Published Applications

**Note: Applicant is not required to submit a paper copy of cited US Published Applications**

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20010046276	2001-11-29	Schneider et al			

## Signature

Examiner Name	Date